

Papers in preparation or submitted

E. Papadomanolaki, L. Lymperakis and **E. Iliopoulos**, "Indium adlayer kinetics on GaN(0001)", *to be submitted in Phys. Rev. B*

E. Papadomanolaki, S.A. Kazazis, L. Lymperakis and **E. Iliopoulos**, "Consistent phenomenological model for the epitaxy of InGaN(0001) alloys by RF-MBE", *to be submitted in J. Appl. Phys.*

S.A. Kazazis, E. Papadomanolaki, M. Androulidaki, M. Kayambaki and **E. Iliopoulos**, "Optical properties of InGaN thin films in the entire composition range", *to be submitted in J. Appl. Phys.*

2017

1. S.A. Kazazis, E. Papadomanolaki and **E. Iliopoulos**, "Polarization effects in InGaN/GaN heterojunctions' photovoltaic operation: Realistic perspectives for single heterojunction InGaN solar cells", *accepted-to appear in IEEE J. Photovolt.*

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2. S.A. Kazazis, E. Papadomanolaki, M. Androulidaki, K. Tsagaraki, A. Kostopoulos, E. Aperathitis and **E. Iliopoulos**, "Effect of rapid thermal annealing on polycrystalline InGaN thin films deposited on fused silica substrates", *Thin Solid Films* **611**, 46 (2016) **Cited: 1(0)**
3. E. Papadomanolaki, C. Bazioti, S.A. Kazazis, M. Androulidaki, G.P. Dimitrakopoulos and **E. Iliopoulos**, "Molecular beam epitaxy of thick InGaN(0001) films: Effects of substrate temperature on structural and electronic properties", *J. Cryst. Growth* **437**, 20 (2016) **Cited: 1(0)**
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6. C. Bazioti, E. Papadomanolaki, Th. Kehagias, T. Walter, J. Smalc-Koziorowska, E. Pavlidou, Ph. Komninou, Th. Karakostas, **E. Iliopoulos**, G.P. Dimitrakopoulos, "Defects, strain relaxation, and compositional grading in high indium content InGaN epilayers grown by molecular beam epitaxy", *J. Appl. Phys.* **118**, 155301 (2015) **Cited: 5(1)**

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